

## 2SK3019-TP Datasheet

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DiGi Electronics Part Number 2SK3019-TP-DG

Manufacturer Micro Commercial Co

Manufacturer Product Number 25K3019-TP

Description MOSFET N-CH 30V 100MA SOT523

**Detailed Description** N-Channel 30 V 100mA (Ta) 150mW (Ta) Surface M

ount SOT-523

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## **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
2SK3019-TP	Micro Commercial Co
Series:	Product Status:
	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
30 V	100mA (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
4V, 10V	80hm @ 10mA, 4V
Vgs(th) (Max) @ ld:	Vgs (Max):
1.5V @ 100μA	±20V
Input Capacitance (Ciss) (Max) @ Vds:	FET Feature:
13 pF @ 5 V	
Power Dissipation (Max):	Operating Temperature:
150mW (Ta)	-55°C ~ 150°C (TA)
Mounting Type:	Supplier Device Package:
Surface Mount	SOT-523
Package / Case:	Base Product Number:
SOT-523	2SK3019

## **Environmental & Export classification**

8541.21.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



## **Features**

- ESD Protected up to 2KV(HBM)
- · Moisture Sensitivity Level 1
- Halogen Free. "Green" Device (Note 1)
- · Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

# N-Channel MOSFET

## **Maximum Ratings**

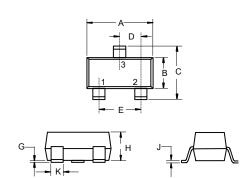
- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature: -55°C to +150°C
- Thermal Resistance: 436°C/W Junction to Ambient(Note 2)

Parameter		Symbol	Rating	Unit	
Drain -source Voltage		V <sub>DS</sub>	30	V	
Gate -Source Voltage	V <sub>GS</sub>	±20	V		
Drain Current-Continuous	T <sub>A</sub> =25°C		100	mA	
	T <sub>A</sub> =100°C	l <sub>D</sub>	63		
Pulsed Drain Current(Note 3)		I <sub>DM</sub>	400	mA	
Power Dissipation(Note 4)		P <sub>D</sub>	0.29	W	

#### Note:

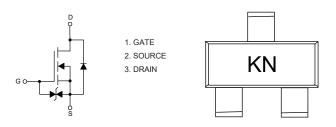
- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. The value of  $R_{\theta JA}$  is measured with the device mounted on  $1in^2$  FR-4 board with 2oz. Copper, in a still air environment with  $T_A$ =25°C.
- 3. Repetitive rating; pulse width limited by max. junction temperature.
- 4. P<sub>D</sub> is based on max. junction temperature, using junction-ambient thermal resistance.

## SOT-523

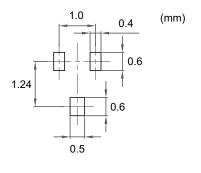


	DIMENSIONS					
DIM	INCHES		MM		NOTE	
DIIVI	MIN	MAX	MIN	MAX	NOTE	
Α	0.059	0.067	1.50	1.70		
В	0.030	0.033	0.75	0.85		
С	0.057	0.069	1.45	1.75		
D	0.020		0.50		TYP.	
E	0.035	0.043	0.90	1.10		
G	0.000	0.004	0.00	0.10		
Н	0.024	0.031	0.60	0.80		
J	0.004	0.008	0.10	0.20		
K	0.006	0.014	0.15	0.35		

## **Internal Structure and Marking Code**



## **Suggested Solder Pad Layout**





## Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit	
Static Characteristics	•		- 1	1		1	
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	30			V	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.8	1	1.5	V	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =± 20V, V <sub>DS</sub> =0V			±2	μA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			100	nA	
		V <sub>GS</sub> =10V, I <sub>D</sub> =500mA		1.8	4		
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =200mA		2	5	Ω	
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =50mA		4	13		
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =100mA		200		mS	
Gate Resistance	$R_g$	f=1 MHz, Open drain		255		Ω	
Diode Characteristics			·				
Continuous Body Diode Current	Is				0.1	Α	
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =500mA			1.4	V	
Reverse Recovery Time	t <sub>rr</sub>	1 = 0 2 A dl /dt= 100 A /u.c		11		ns	
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> =0.3A, dI <sub>F</sub> /dt=100A/μs		3		nC	
Dynamic Characteristics							
Input Capacitance	C <sub>iss</sub>			16			
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =15V,V <sub>GS</sub> =0V,f=1MHz		5.4		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			3.3			
Total Gate Charge	Q <sub>g</sub>			0.78			
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =15V,V <sub>GS</sub> =10V,I <sub>D</sub> =0.3A		0.13		nC	
Gate-Drain Charge	$Q_{gd}$			0.14			
Turn-On Delay Time	t <sub>d(on)</sub>			2.4			
Turn-On Rise Time	t <sub>r</sub>	V <sub>DD</sub> =15V,V <sub>GS</sub> =10V,		2.7			
Turn-Off Delay Time	t <sub>d(off)</sub>	$R_G=3.9\Omega, I_D=0.3A$		6		ns ns	
Turn-Off Fall Time	t <sub>f</sub>			10			



### **Curve Characteristics**

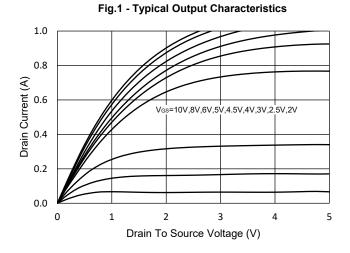


Fig.2 - Transfer Characteristic

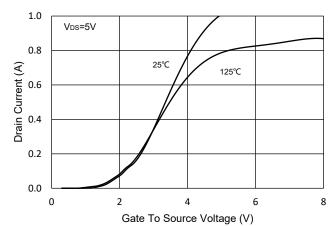


Fig.3 -  $R_{DS(ON)}$  -  $V_{GS}$ 

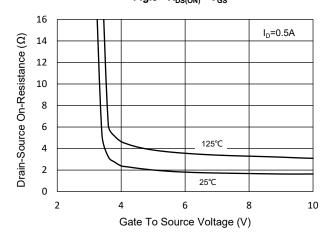


Fig.4 -  $R_{\rm DS(ON)}$  -  $I_{\rm D}$ 

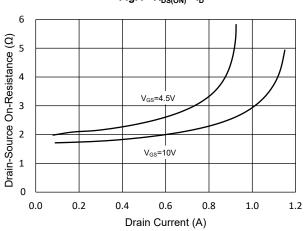


Fig.5 - Capacitance Characteristics

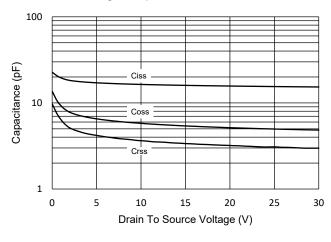
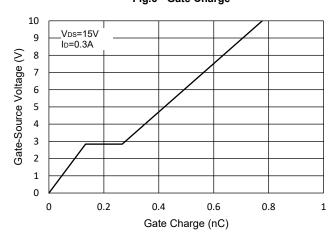


Fig.6 - Gate Charge





## **Curve Characteristics**

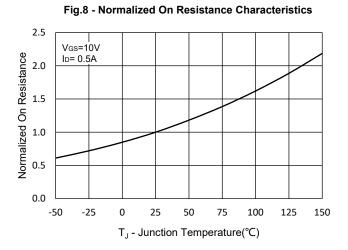
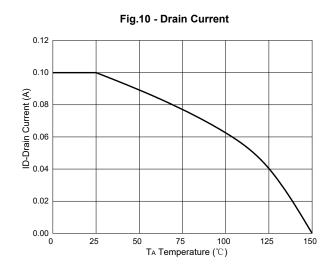
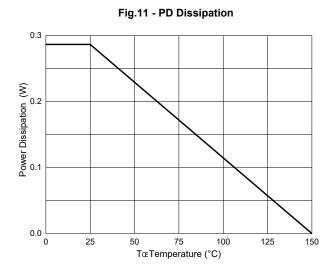


Fig.9 -  $I_S$  -  $V_{SD}$ 10  $V_{GS} = 0V$ 1 Source Current (A) 25°C 0.1 0.01 0.001 0.0 0.2 0.4 0.6 0.8 1.0 1.2 1.4 Source To Drain Voltage (V)







### **Curve Characteristics**

Fig.12 - Safe Operation Area

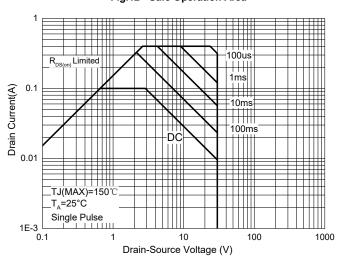
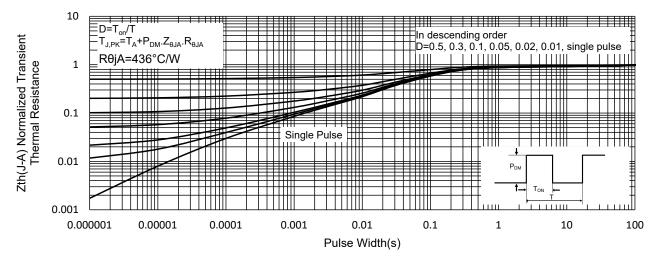


Fig.13 - Normalized Transient Thermal Impedance





## **Ordering Information**

Device	Packing		
Part Number-TP	Tape&Reel:3Kpcs/Reel		

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